

**CERTIFICATE OF MAILING BY FIRST CLASS MAIL (37 CFR 1.8)**

Applicant(s): Cheng et al.

Docket No.

N1085-90166

Application No.

10/728,215

Filing Date

12/4/2003

Examiner

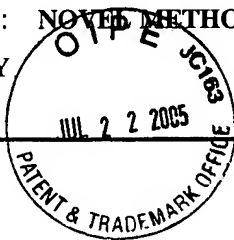
Laura M. Schillinger

Customer No.

08933

Group Art Unit

283

Invention: **NOVEL METHOD TO DEPOSIT CARBON DOPED SiO<sub>2</sub> FILMS WITH IMPROVED FILM QUALITY**I hereby certify that this Election; certificate of mailing; postcard

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is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450" [37 CFR 1.8(a)] on

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

<b>In Re Patent Application:</b>	:	<b>Group Art Unit: 2813</b>
Yi-Lung Cheng et al.	:	
<b>Serial Number:</b> 10/728,215	:	<b>Examiner:</b> Laura M. Schillinger
	:	
<b>Filed:</b> December 4, 2003	:	<b>Atty Docket No.:</b> 2003-0395/N1085-90166
	:	
<b>Title:</b> Novel Method To Deposit Carbon Doped SiO <sub>2</sub> Films With Improved Film Quality	:	<b>Date:</b> July 19, 2005
	:	
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Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**ELECTION**

Sir:

This communication is responsive to the Office Action mailed on June 21, 2005, in the above-captioned application, wherein claims 1-28 stand subject to a restriction or election requirement under 35 U.S.C. 121. In support of the requirement, the Examiner states that the application contains claims directed to the following patentably distinct species:

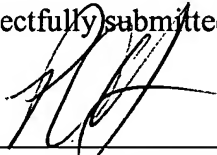
Species 1, claims 1-10, pertaining to a method including forming a plasma to deposit C-doped SiO<sub>2</sub> at certain reaction conditions and continuing until acceptable film thickness is reached on a substrate;

Species 2, claims 11-28, pertaining to a method including forming a plasma to deposit a low-k dielectric layer comprising C-doped SiO<sub>2</sub> on an etch stop and forming an opening to the etch stop and depositing metal.

The Applicant elects species 1, directed to a method of depositing a carbon doped SiO<sub>2</sub> film on a substrate, for prosecution on the merits. This election is made without traverse. Claims 1-10 read on the elected species 1.

No fees are due with this communication. The Commissioner is hereby authorized to charge payment of any additional filing fees required under 37 CFR 1.16 and any patent application processing fees under 37 CFR 1.17, which are associated with this communication, or credit any overpayment to Deposit Account No. 50-2061.

Respectfully submitted,



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